

PD57006-01 RF POWER TRANSISTORS The LdmoST Plastic FAMILY TARGET DATA

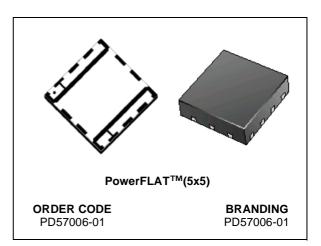
N-CHANNEL ENHANCEMENT-MODE LATERAL MOSFETs

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- P_{OUT} = 6 W with 15 dB gain @ 945 MHz / 28V
- NEW LEADLESS PLASTIC PACKAGE

DESCRIPTION

The PD57006-01 is a common source N-Channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broad band commercial and industrial applications. It operates at 28 V in common source mode at frequencies of up to 1 GHz. PD57006-01 boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology mounted in the innovative leadless SMD plastic package, PowerFLATTM.

It is ideal for digital cellular BTS applications requiring high linearity.



ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 2\5 °C)

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-Source Voltage	65	V
V _{GS}	Gate-Source Voltage	± 20	V
Ι _D	Drain Current	1	А
PDISS	Power Dissipation (@ Tc = 70°C)	TBD	W
Tj	Max. Operating Junction Temperature	150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

R _{th(j-c)} Junction -Case Thermal Resistance	TBD	°C/W
--	-----	------

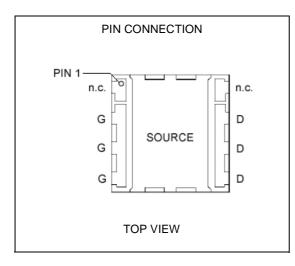
ELECTRICAL SPECIFICATION (T_{CASE} = 25 °C)

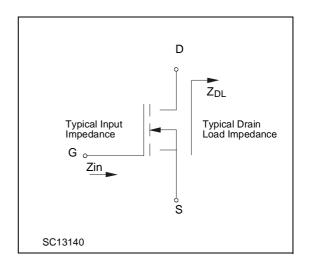
STATIC

Symbol	Test Conditions		Min.	Тур.	Max.	Unit	
V _{(BR)DSS}	$V_{GS} = 0 V$	I _D = 10 mA		65			
I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 28 V				1	μA
I _{GSS}	V _{GS} = 20 V	$V_{DS} = 0 V$				1	μA
V _{GS(Q)}	V _{DS} = 28 V	I _D = 70 mA		2.0		5.0	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 0.5 A				0.9	V
9 FS	V _{DS} = 10 V	I _D = 800 mA			0.58		mho
C _{ISS}	$V_{GS} = 0 V$	V _{DS} = 28 V	f = 1 MHz		27		pF
C _{OSS}	$V_{GS} = 0 V$	V _{DS} = 28 V	f = 1 MHz		14		pF
C _{RSS}	$V_{GS} = 0 V$	V _{DS} = 28 V	f = 1 MHz		0.9		pF

DYNAMIC

Symbol	Test Conditions			Тур.	Max.	Unit
Pout	$V_{DD} = 28 \text{ V}$ $I_{DQ} = 70 \text{ mA}$	f = 945 MHz	6			W
GP	$V_{DD} = 28 \text{ V}$ $I_{DQ} = 70 \text{ mA}$ $P_{OUT} = 6 \text{ V}$	/ f = 945 MHz	14	15		dB
η _D	$V_{DD} = 28 \text{ V}$ $I_{DQ} = 70 \text{ mA}$ $P_{OUT} = 6 \text{ V}$	/ f = 945 MHz	45	50		%
Load mismatch	$V_{DD} = 28 V$ $I_{DQ} = 70 mA$ $P_{OUT} = 6 V$ ALL PHASE ANGLES	/ f = 945 MHz	10:1			VSWR





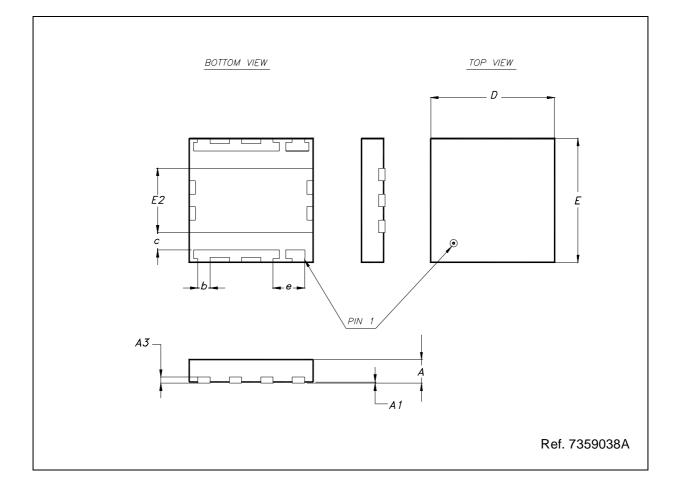
IMPEDANCE DATA

PD57006						
FREQ. MHz	Ζ_{ΙΝ} (Ω)	Ζ_{DL}(Ω)				
925	TBD	TBD				
945	TBD	TBD				
960	TBD	TBD				

57

		mm Inch				
DIM.	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A		0.90	1.00		0.035	0.039
A1		0.02	0.05		0.001	0.002
A3		0.24			0.009	
b	0.43	0.51	0.58	0.017	0.020	0.023
С	0.64	0.71	0.79	0.025	0.028	0.031
D		5.00			0.197	
E		5.00			0.197	
E2	2.49	2.57	2.64	0.098	0.101	0.104
e		1.27			0.050	





Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is registered trademark of STMicroelectronics (B) 2002 STMicroelectronics - All Rights Reserved

All other names are the property of their respective owners.

STMicroelectronics GROUP OF COMPANIES Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A. http://www.st.com

